IN THE CLAIMS

Please amend the claims as follows:

Claims 1-5 (Cancelled).

Claim 6 (Currently amended): A method for producing a silicon oxide film comprising ~~the step of~~ forming a silicon oxide film by thermochemical vapor-phase deposition at ~~the~~ a pressure ~~in the range from~~ of 0.01mmHg to 2 atm using ~~a silane~~ an alkoxydisilane compound of the formula

$H_nSi_2(OR)_{6-n}$

wherein

R is an alkyl group of carbon number from 1 to 6, and n is an integer from 0 to 5 and a diluting gas.

Claim 7 (Currently amended): The method for producing a silicon oxide film according to Claim [[1]] 6, wherein said silicon oxide film is formed by plasma chemical vapor-phase deposition.

Claim 8 (Currently amended): The method for producing a silicon oxide film according to Claim [[1]] 6, wherein ozone is used as an oxidizing agent.

Claim 9 (Currently amended): The method for producing a silicon oxide film according to Claim [[1]] 6, wherein the deposition temperature is ~~controlled to the range~~ from 200 to 500°C.

Claim 10 (Currently amended): A method for manufacturing a semiconductor device comprising ~~the step of~~ depositing an insulating film comprising a silicon oxide film of Claim [[1]] 6.

Claim 11 (New): The method for producing a silicon oxide film according to Claim 6, wherein said alkoxydisilane is a monoalkoxydisilane.

Claim 12 (New): The method for producing a silicon oxide film according to Claim 11, wherein said monoalkoxydisilane is selected from the group consisting of monomethoxydisilane, monoethoxydisilane, monopropoxydisilane, and monobutoxydisilane.

Claim 13 (New): The method for producing a silicon oxide film according to Claim 6, wherein said alkoxydisilane is a dialkoxydisilane.

Claim 14 (New): The method for producing a silicon oxide film according to Claim 13, wherein said dialkoxydisilane is selected from the group consisting of dimethoxydisilane, diethoxydisilane, propoxydisilane, and dibutoxydisilane.

Claim 15 (New): The method for producing a silicon oxide film according to Claim 6, wherein said alkoxydisilane is a trialkoxydisilane.

Claim 16 (New): The method for producing a silicon oxide film according to Claim 15, wherein said trialkoxydisilane is selected from the group consisting of trimethoxydisilane, triethoxydisilane, tripropoxydisilane, and tributoxydisilane.

Claim 17 (New): The method for producing a silicon oxide film according to Claim 6, wherein said alkoxydisilane is a tetraalkoxydisilane.

Claim 18 (New): The method for producing a silicon oxide film according to Claim 17, wherein said tetraalkoxydisilane is selected from the group consisting of tetramethoxydisilane, tetraethoxydisilane, tetrapropoxydisilane, and tetrabutoxydisilane.

Claim 19 (New): The method for producing a silicon oxide film according to Claim 6, wherein said alkoxydisilane is a pentaalkoxydisilane.

Claim 20 (New): The method for producing a silicon oxide film according to Claim 19, wherein said pentaalkoxydisilane is selected from the group consisting of pentamethoxydisilane, pentaethoxydisilane, pentapropoxydisilane, and pentabutoxydisilane.

Claim 21 (New): The method for producing a silicon oxide film according to Claim 6, wherein said alkoxydisilane is a hexaalkoxydisilane.

Claim 22 (New): The method for producing a silicon oxide film according to Claim 21, wherein said hexaalkoxydisilane is selected from the group consisting of hexamethoxydisilane, hexaethoxydisilane, hexapropoxydisilane, and hexabutoxydisilane.

Claim 23 (New): The method for producing a silicon oxide film according to Claim 6, wherein said alkoxydisilane is tetraethoxydisilane.

Claim 24 (New): The method for producing a silicon oxide film according to Claim 6, wherein said alkoxydisilane is hexaethoxydisilane.